

STARPOWER

SEMICONDUCTOR

IGBT

GD150HFX65C1S

650V/150A 2 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

Features

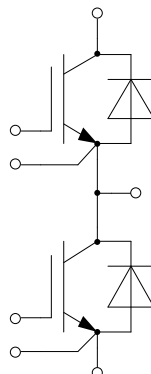
- Low $V_{CE(sat)}$ Trench IGBT technology
- 6 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	650	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	200	A
	@ $T_C=55^{\circ}\text{C}$	150	
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	300	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	416	W

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	650	V
I_F	Diode Continuous Forward Current	150	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	300	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	2500	V

IGBT Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=150\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		1.45	1.90	V
		$I_C=150\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		1.60		
		$I_C=150\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$		1.70		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=2.4\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.1	5.8	6.4	V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			1.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA
R_{Gint}	Internal Gate Resistance			2.0		Ω
C_{ies}	Input Capacitance	$V_{CE}=30\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		9.24		nF
C_{res}	Reverse Transfer Capacitance			0.27		nF
Q_G	Gate Charge	$V_{GE}=-15 \dots +15\text{V}$		1.60		μC
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300\text{V}, I_C=150\text{A}, R_G=3.3\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		94		ns
t_r	Rise Time			24		ns
$t_{d(off)}$	Turn-Off Delay Time			276		ns
t_f	Fall Time			49		ns
E_{on}	Turn-On Switching Loss			0.67		mJ
E_{off}	Turn-Off Switching Loss			3.28		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300\text{V}, I_C=150\text{A}, R_G=3.3\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		112		ns
t_r	Rise Time			31		ns
$t_{d(off)}$	Turn-Off Delay Time			296		ns
t_f	Fall Time			55		ns
E_{on}	Turn-On Switching Loss			1.08		mJ
E_{off}	Turn-Off Switching Loss			4.25		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300\text{V}, I_C=150\text{A}, R_G=3.3\Omega, V_{GE}=\pm 15\text{V}, T_j=150^\circ\text{C}$		113		ns
t_r	Rise Time			32		ns
$t_{d(off)}$	Turn-Off Delay Time			305		ns
t_f	Fall Time			56		ns
E_{on}	Turn-On Switching Loss			1.21		mJ
E_{off}	Turn-Off Switching Loss			4.46		mJ
I_{SC}	SC Data	$t_P \leq 6\mu\text{s}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}, V_{CC}=360\text{V}, V_{CEM} \leq 650\text{V}$		750		A

Diode Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=150\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.55	2.00	V
		$I_F=150\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		1.50		
		$I_F=150\text{A}, V_{GE}=0\text{V}, T_j=150^\circ\text{C}$		1.45		
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=150\text{A},$ $-di/dt=5940\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		7.81		μC
I_{RM}	Peak Reverse Recovery Current			167		A
E_{rec}	Reverse Recovery Energy			2.13		mJ
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=150\text{A},$ $-di/dt=5940\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		14.3		μC
I_{RM}	Peak Reverse Recovery Current			198		A
E_{rec}	Reverse Recovery Energy			3.85		mJ
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=150\text{A},$ $-di/dt=5940\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^\circ\text{C}$		16.2		μC
I_{RM}	Peak Reverse Recovery Current			204		A
E_{rec}	Reverse Recovery Energy			4.33		mJ

Module Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
R_{thJC}	Junction-to-Case (per IGBT)			0.360	K/W
	Junction-to-Case (per Diode)			0.600	
R_{thCH}	Case-to-Heatsink (per IGBT)		0.160		K/W
	Case-to-Heatsink (per Diode)		0.267		
	Case-to-Heatsink (per Module)		0.050		
M	Terminal Connection Torque, Screw M5	2.5		5.0	N.m
	Mounting Torque, Screw M6	3.0		5.0	
G	Weight of Module		150		g

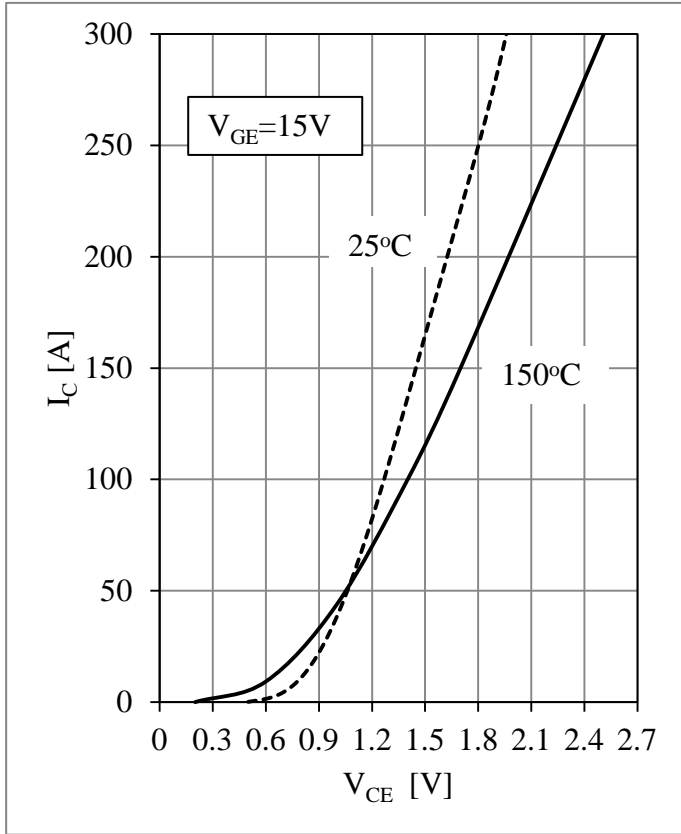


Fig 1. IGBT Output Characteristics

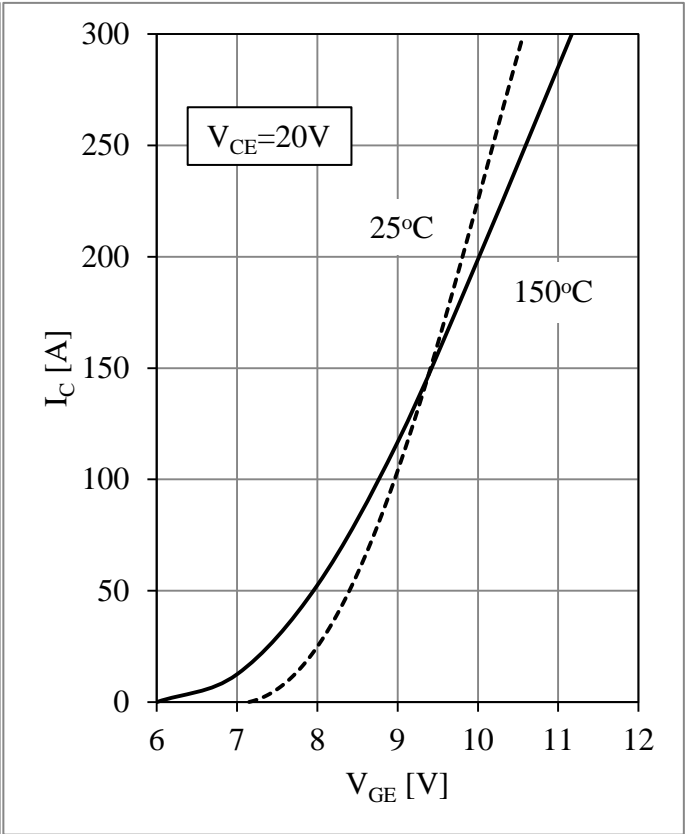


Fig 2. IGBT Transfer Characteristics

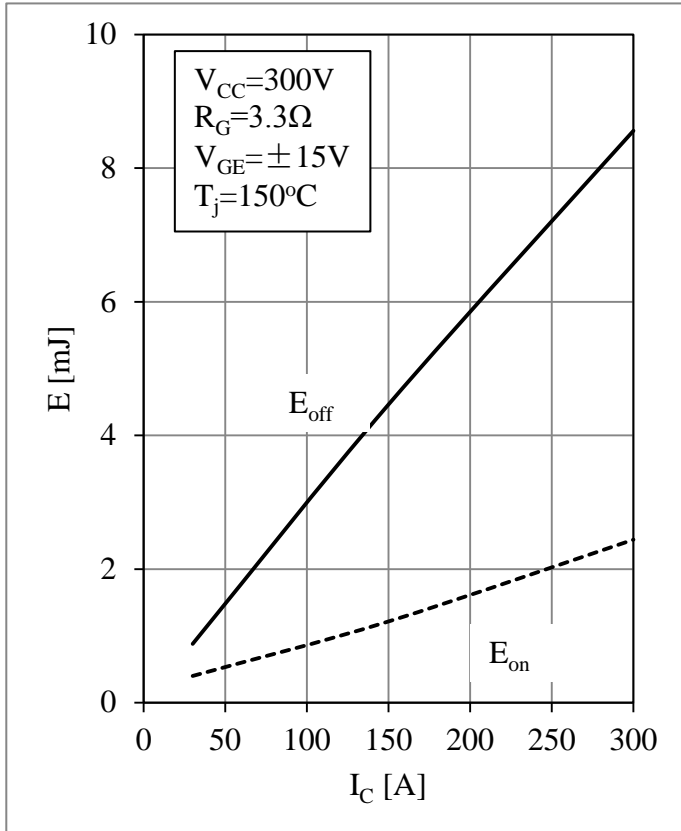


Fig 3. IGBT Switching Loss vs. I_C

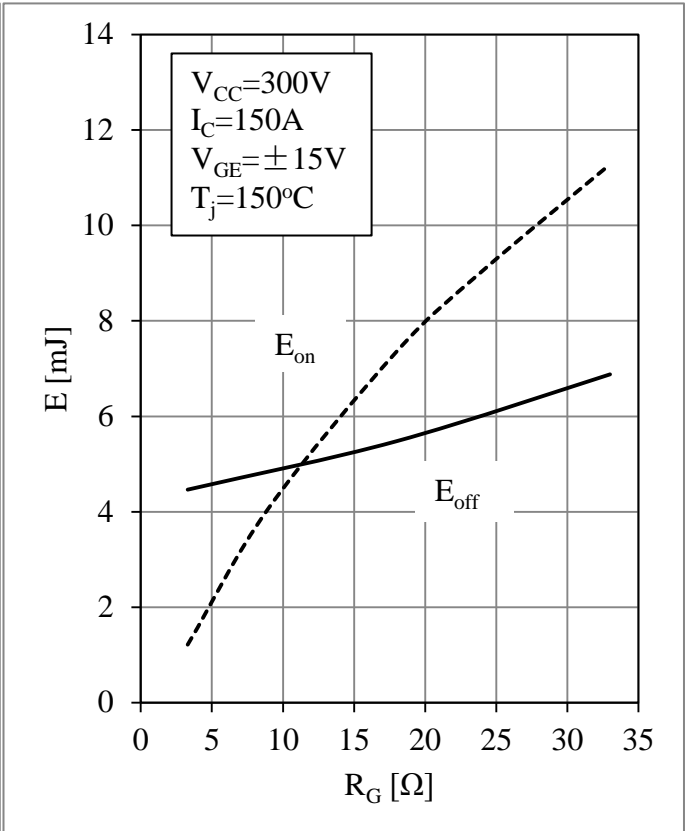


Fig 4. IGBT Switching Loss vs. R_G

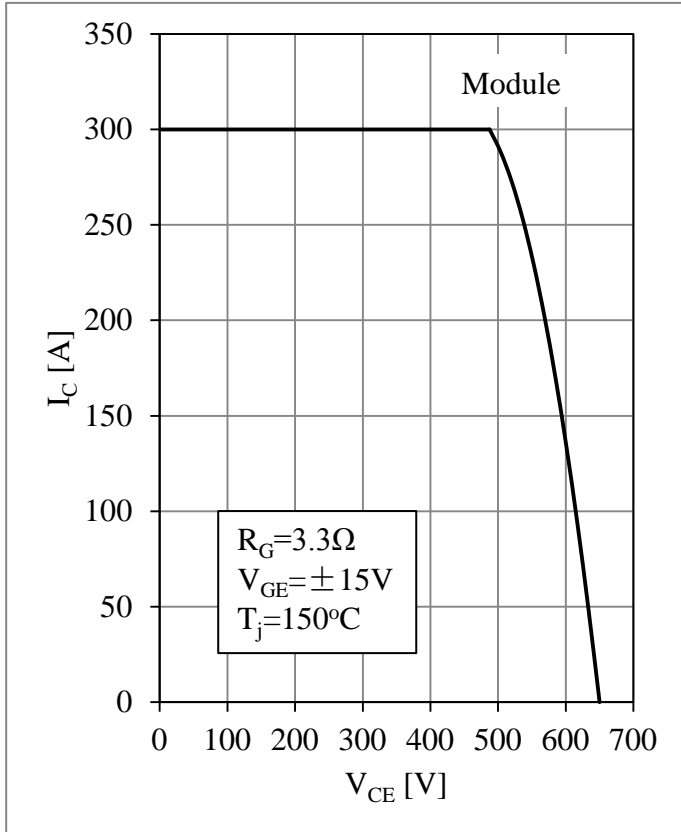


Fig 5. RBSOA

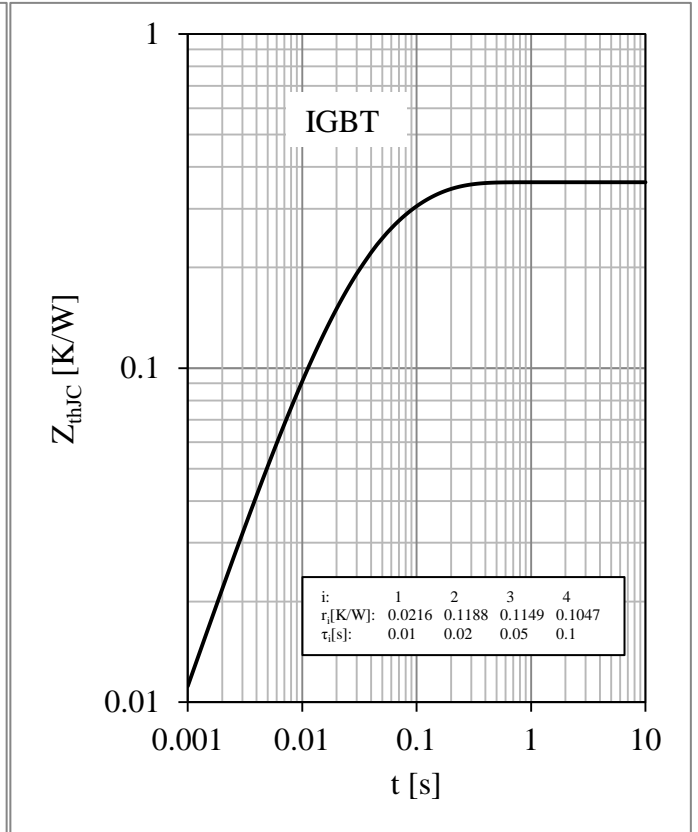


Fig 6. IGBT Transient Thermal Impedance

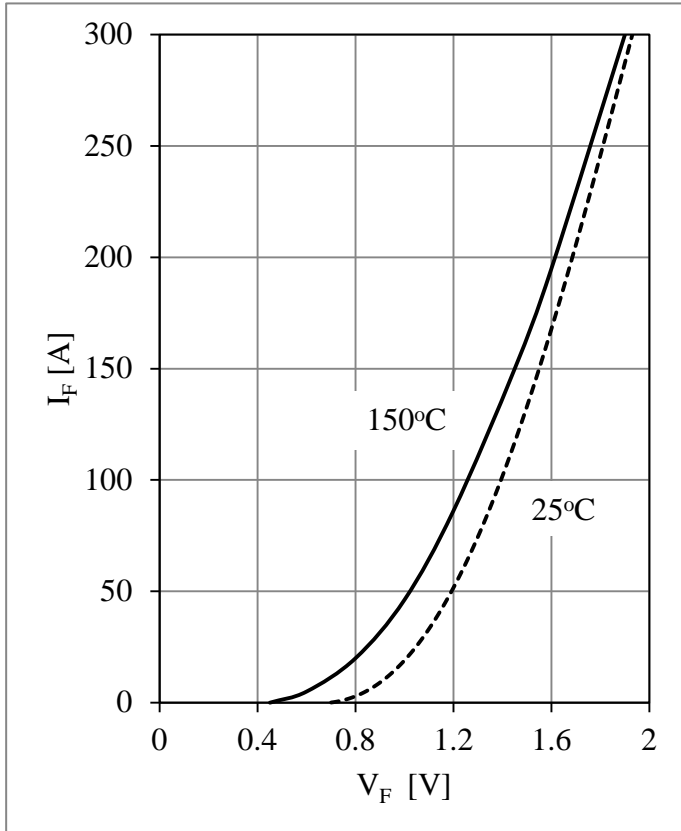


Fig 7. Diode Forward Characteristics

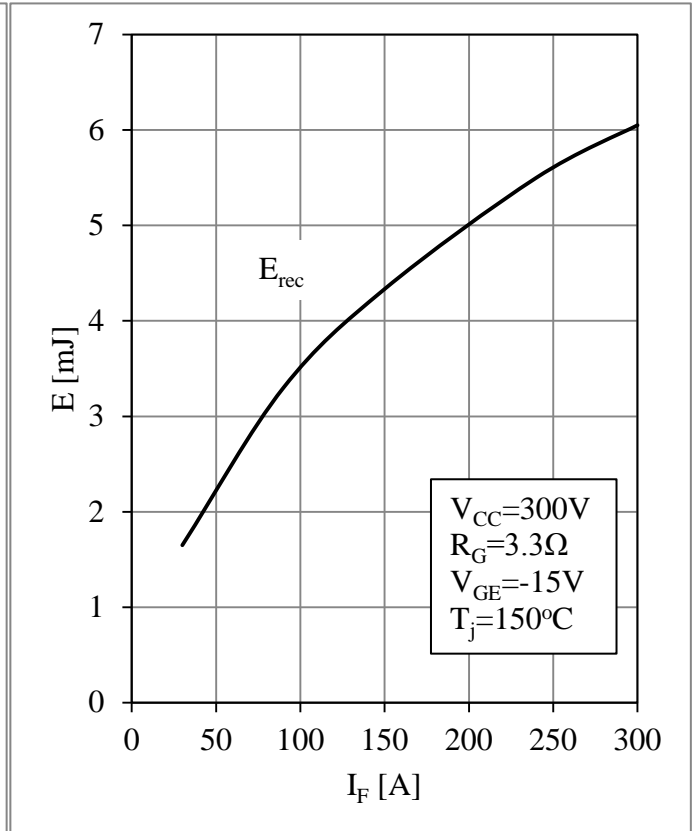


Fig 8. Diode Switching Loss vs. I_F

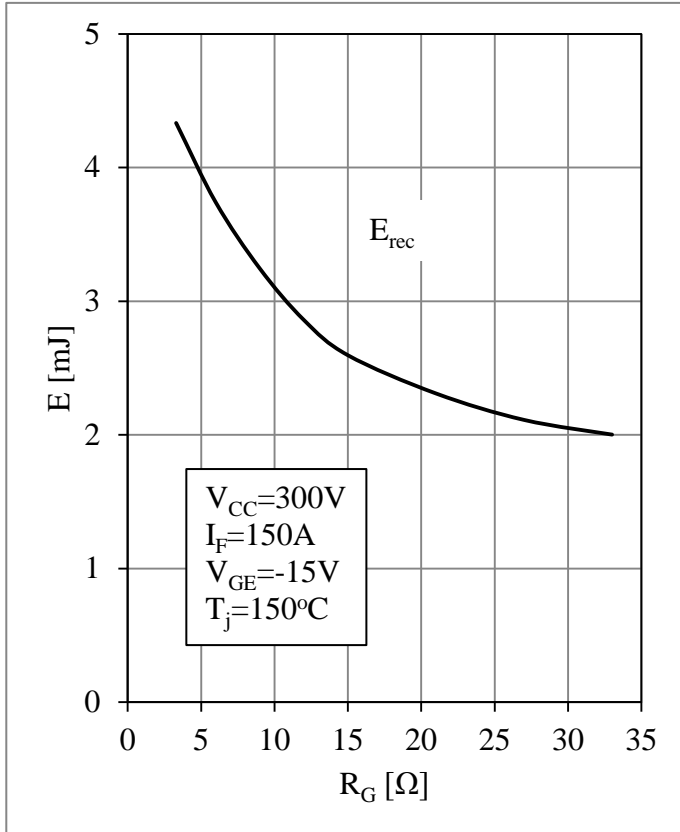


Fig 9. Diode Switching Loss vs. R_G

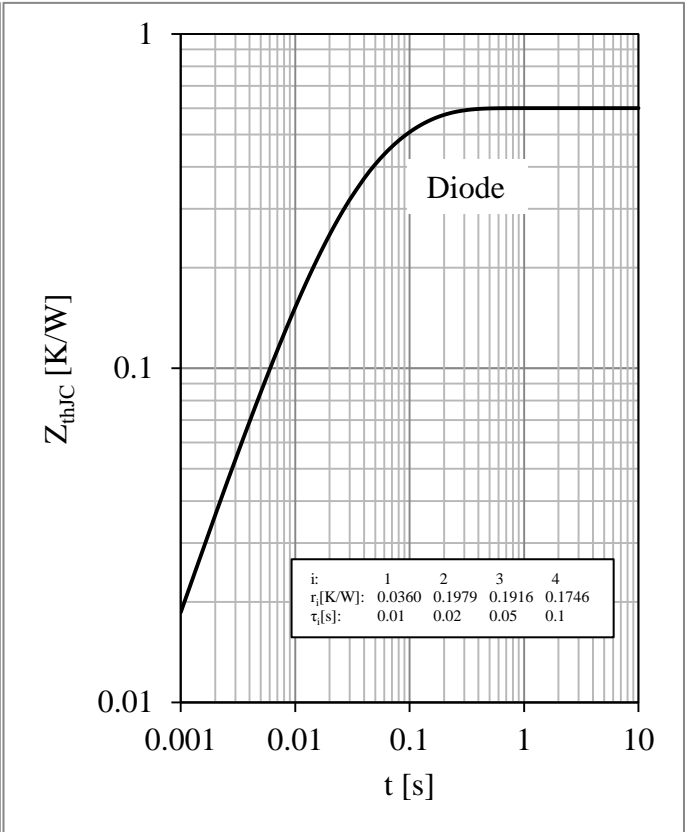
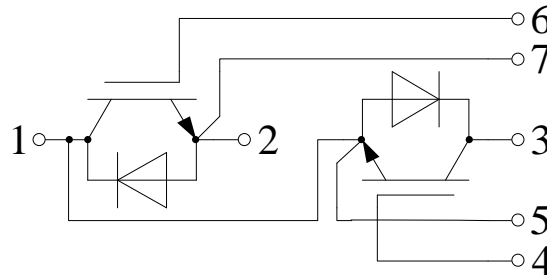
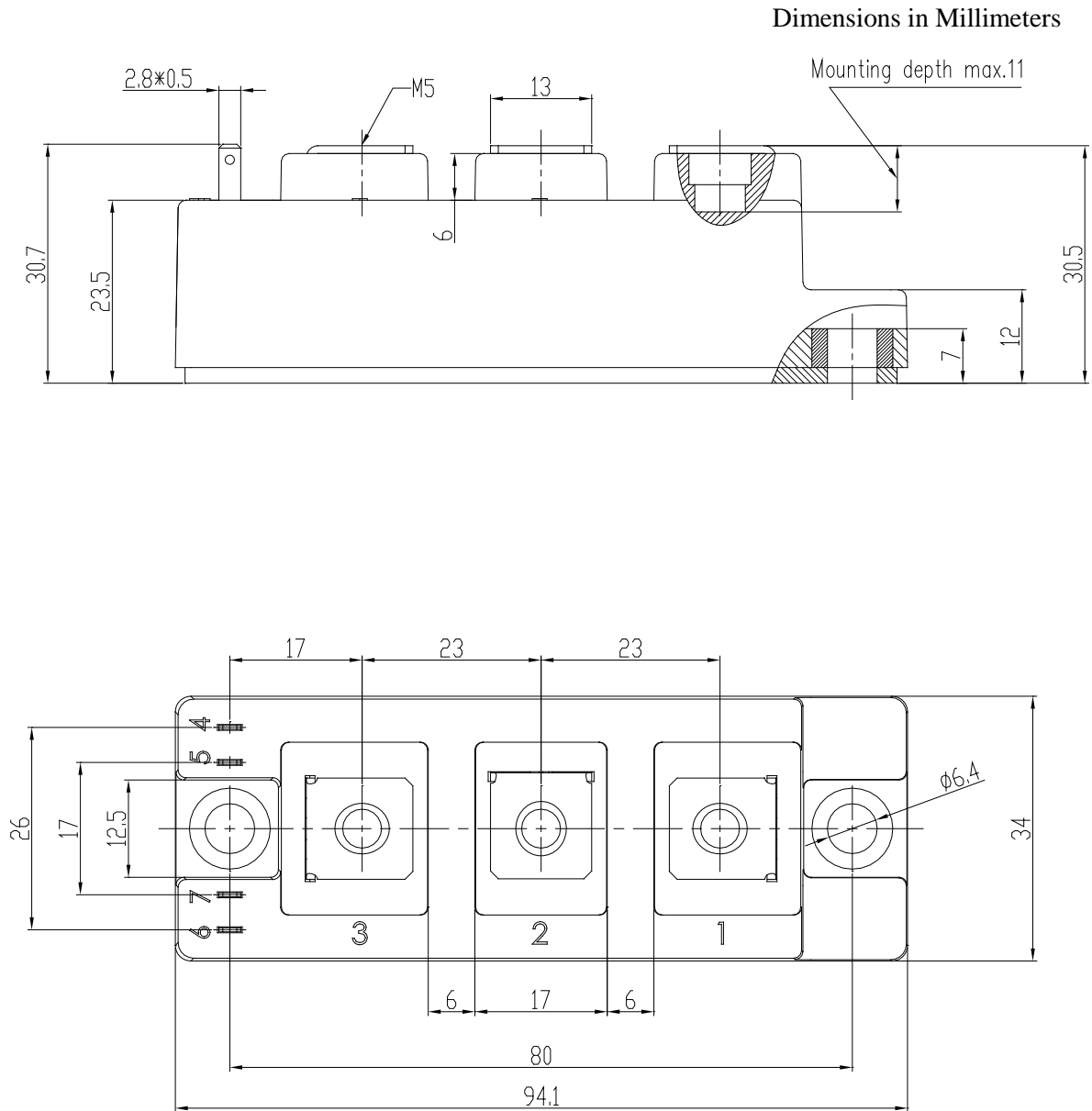


Fig 10. Diode Transient Thermal Impedance

Circuit Schematic



Package Dimensions



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